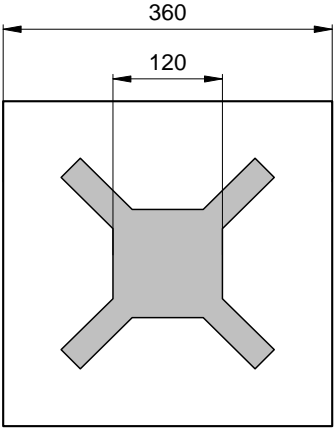


Radiation	Type	Technology	Electrodes
Infrared	DH	AlGaAs/GaAs	P (anode) up

 <p style="text-align: center;">LED-14</p>	typ. dimensions (μm)
	<u>typ. thickness</u> 260 (±20) μm <u>anode</u> gold alloy, 1.5 μm <u>cathode</u> gold alloy, 0.5 μm,

Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I _F			100	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F	1.1	1.2	1.4	V
Reverse voltage	I _R = 100 μA	V _R	5			V
Radiant power*	I _F = 20 mA	Φ _e	1.5	2,5		mW
Peak wavelength	I _F = 20 mA	λ _p	920	935	950	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}	50	70	90	nm
Switching time	I _F = 20 mA	t _r , t _f		1000	1500	ns

*Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-935-17				

Packing: Chips on adhesive film with wire-bond side on top